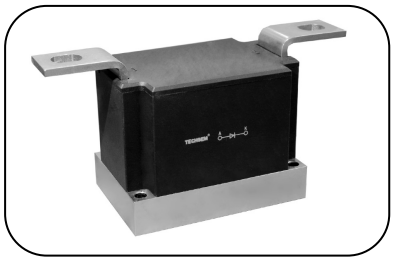


Features：

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{RSM}	V_{RRM}	Type & Outline
900V	800V	MD1000-08-432F2
1100V	1000V	MD1000-10-432F2
1300V	1200V	MD1000-12-432F2
1500V	1400V	MD1000-14-432F2
1700V	1600V	MD1000-16-432F2
1900V	1800V	MD1000-18-432F2

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(℃)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100℃	150			1000	A
$I_{F\ (RMS)}$	RMS forward current		150			1570	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			50	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}	150			28	kA
I^2t	I^2t for fusing coordination					3920	A^2s*10^3
V_{FO}	Threshold voltage		150			0.71	V
r_F	Forward slope resistance					0.10	mΩ
V_{FM}	Peak forward voltage	I_{FM}=3000A	25			1.82	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine, Single side cooled per chip				0.052	℃/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	At 180° sine, Single side cooled per chip				0.020	℃/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min, I_{iso}:1mA(max)		2500			V
F_m	Terminal connection torque(M12)				14.0		N·m
	Mounting torque(M8)				12.0		N·m
T_{vj}	Junction temperature			-40		150	℃
T_{stg}	Stored temperature			-40		125	℃
W_t	Weight				2700		g
Outline	432F2						

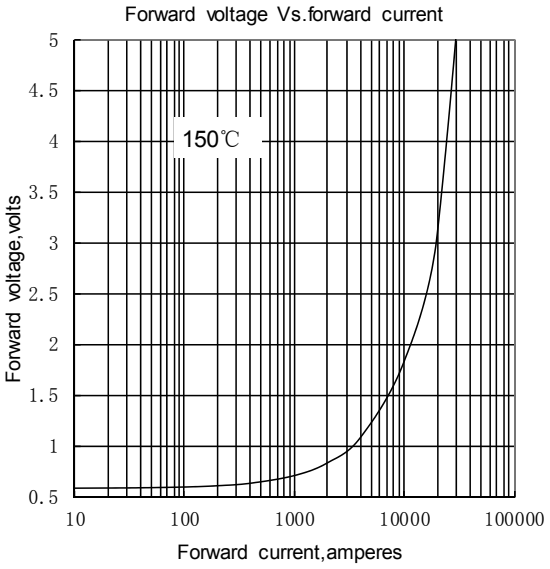


Fig.1

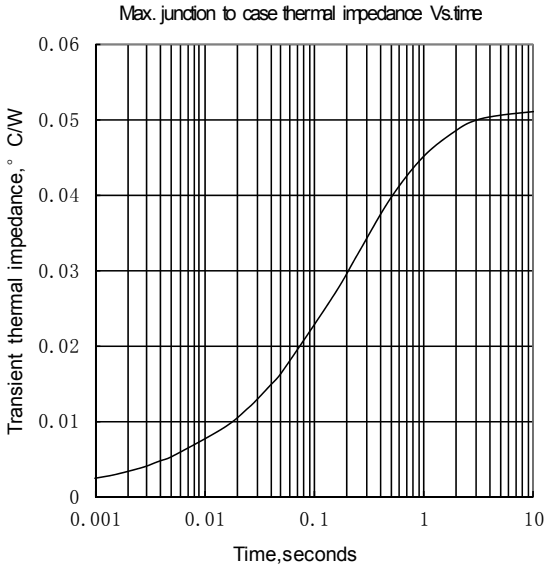


Fig.2

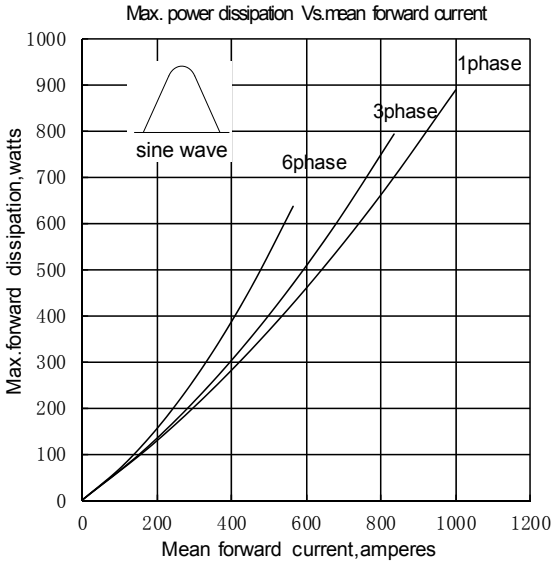


Fig.3

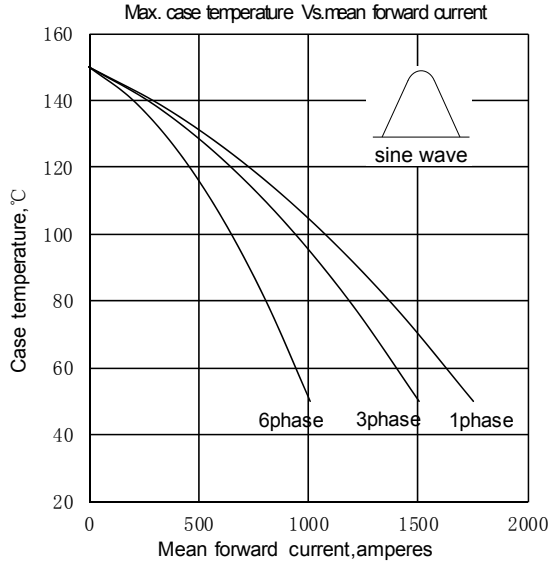


Fig.4

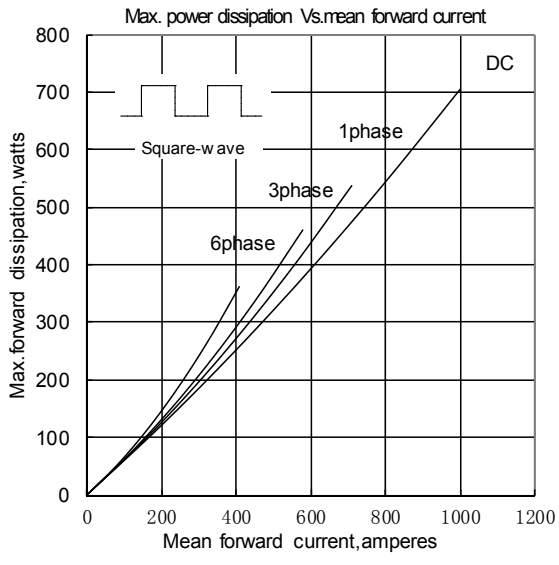


Fig.5

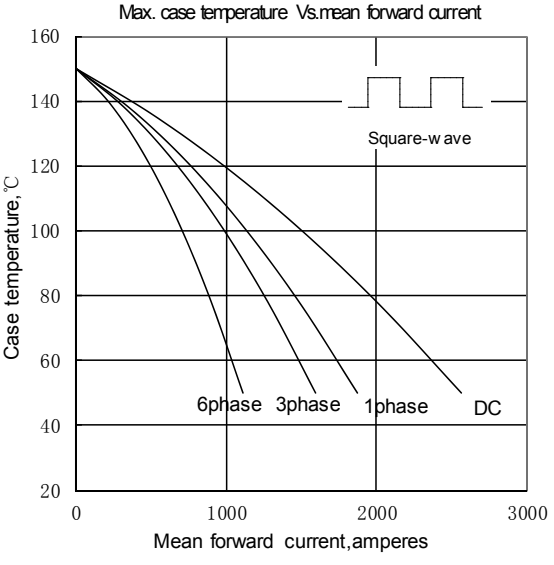


Fig.6

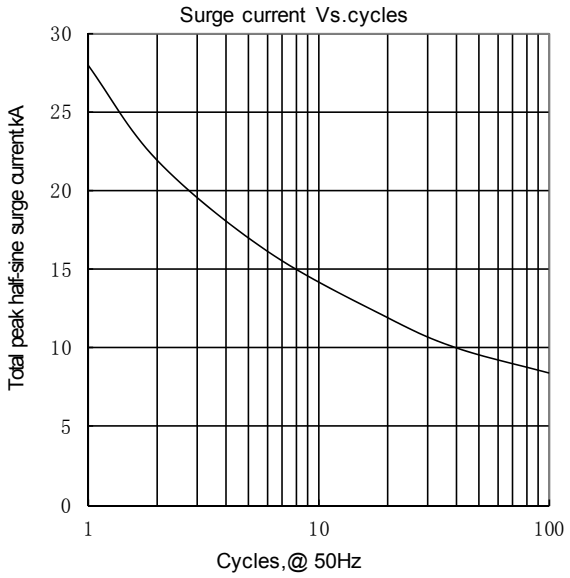


Fig.7

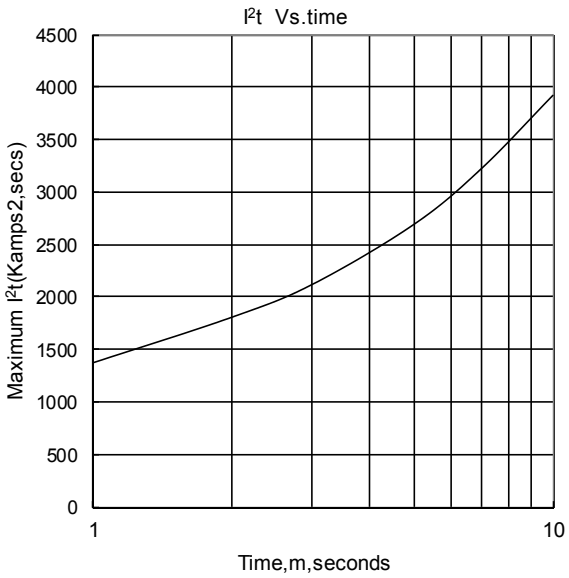
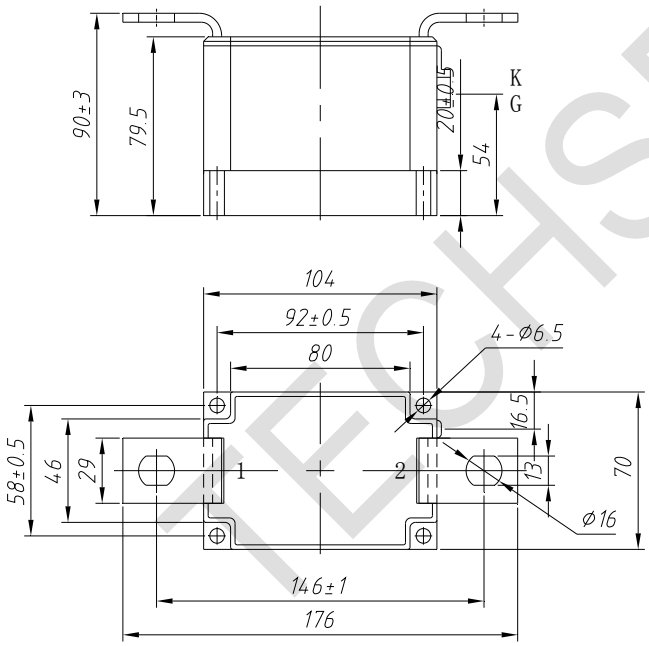


Fig.8

Outline:



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